

HIGH VOLTAGE POWER SCHOTTKY RECTIFIER

MAIN PRODUCT CHARACTERISTICS

$I_{F(AV)}$	2 x 15 A
V_{RRM}	60 V
$T_j(max)$	150°C
$V_F(max)$	0.75 V

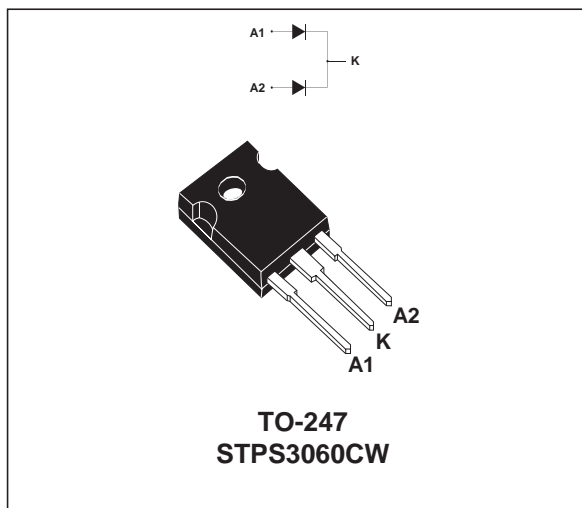
FEATURES AND BENEFITS

- Negligible switching losses
- Low forward voltage drop
- Low capacitance
- High reverse avalanche surge capability.

DESCRIPTION

High voltage dual Schottky rectifier suited for switchmode power supplies and other power converters.

Packaged in TO-247, this device is intended for use in medium voltage operation, and particularly, in high frequency circuitries where low switching losses and low noise are required.



ABSOLUTE RATINGS (limiting values, per diode)

Symbol	Parameter			Value	Unit
V_{RRM}	Repetitive peak reverse voltage			60	V
$I_{F(RMS)}$	RMS forward current		Per diode	30	A
$I_{F(AV)}$	Average forward current $\delta = 0.5$	$T_c = 130^\circ\text{C}$	Per diode Per device	15 30	A
I_{FSM}	Surge non repetitive forward current	$t_p = 10\text{ ms}$ Sinusoidal	Per diode	200	A
I_{RRM}	Repetitive peak reverse current	$t_p = 2\text{ }\mu\text{s}$ $F = 1\text{ kHz}$	Per diode	1	A
I_{RSM}	Non repetitive peak reverse current	$t_p = 100\text{ }\mu\text{s}$	Per diode	1	A
T_{stg}	Storage temperature range			- 65 to + 150	°C
T_j	Maximum operating junction temperature *			150	°C
dV/dt	Critical rate of rise of reverse voltage			1000	V/ μs

* : $\frac{dP_{tot}}{dT_j} < \frac{1}{R_{th(j-a)}}$ thermal runaway condition for a diode on its own heatsink

THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	Junction to case	Per diode	1.5	$^{\circ}\text{C/W}$
		Total	0.8	
$R_{th(c)}$		Coupling	0.1	$^{\circ}\text{C/W}$

When the diodes 1 and 2 are used simultaneously :
 $\Delta T_j(\text{diode 1}) = P(\text{diode 1}) \times R_{th(j-c)}(\text{Per diode}) + P(\text{diode 2}) \times R_{th(c)}$

STATIC ELECTRICAL CHARACTERISTICS (per diode)

Symbol	Parameter	Tests Conditions		Min.	Typ.	Max.	Unit
I_R^*	Reverse leakage current	$T_j = 25^{\circ}\text{C}$	$V_R = V_{RRM}$			150	μA
		$T_j = 125^{\circ}\text{C}$				100	mA
V_F^*	Forward voltage drop	$T_j = 25^{\circ}\text{C}$	$I_F = 15\text{ A}$			0.85	V
		$T_j = 125^{\circ}\text{C}$	$I_F = 15\text{ A}$		0.65	0.75	
		$T_j = 25^{\circ}\text{C}$	$I_F = 30\text{ A}$			1.05	
		$T_j = 125^{\circ}\text{C}$	$I_F = 30\text{ A}$		0.80	0.90	

Pulse test: * $t_p = 5\text{ ms}$, $\delta < 2\%$

** $t_p = 380\mu\text{s}$, $\delta < 2\%$

To evaluate the maximum conduction losses use the following equation :

$$P = 0.6 \times I_{F(AV)} + 0.01 I_F^2(RMS)$$

Fig. 1: Conduction losses versus average current (per diode).

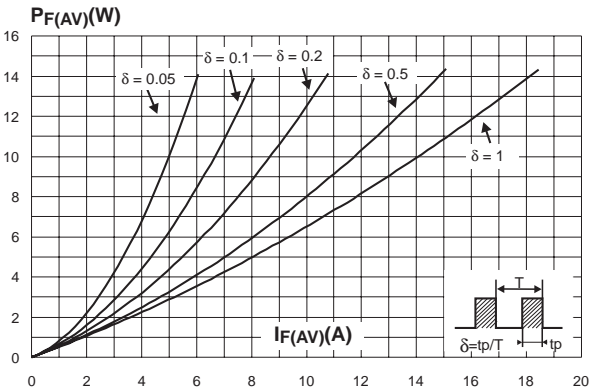


Fig. 2: Average forward current versus ambient temperature ($\delta=0.5$, per diode).

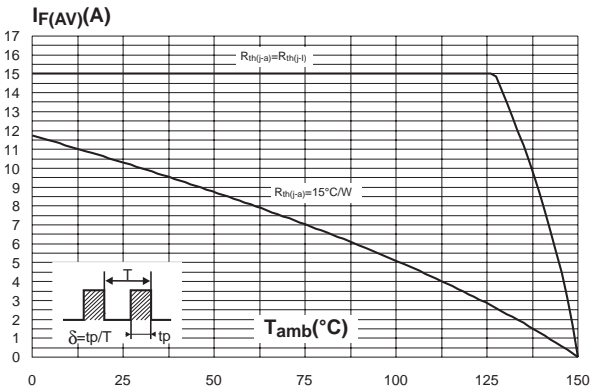


Fig. 3: Non repetitive surge peak forward current versus overload duration (maximum values, per diode).

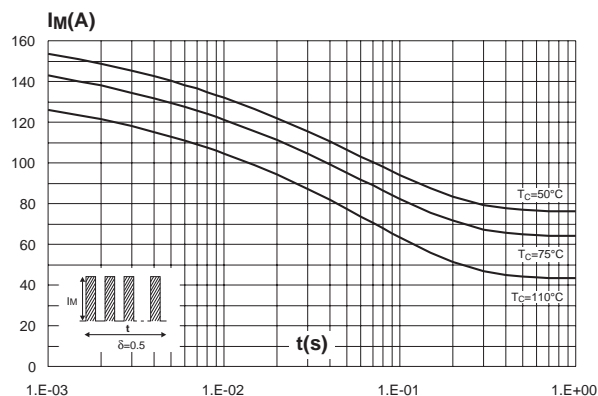


Fig. 4: Relative variation of thermal impedance junction to case versus pulse duration.

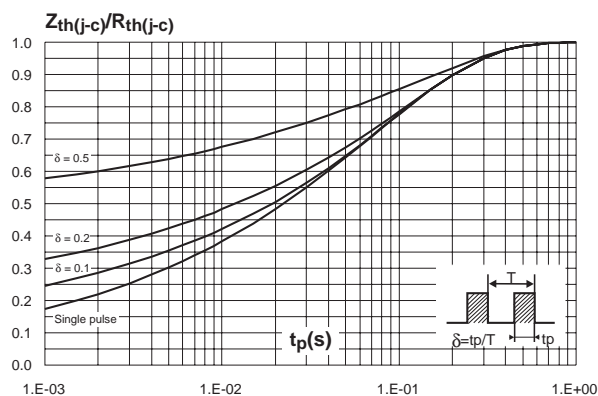


Fig. 5: Reverse leakage current versus reverse voltage applied (typical values, per diode).

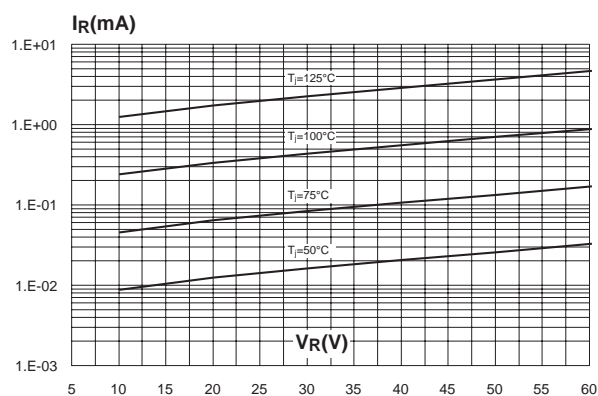


Fig. 6: Junction capacitance versus reverse voltage applied (typical values, per diode).

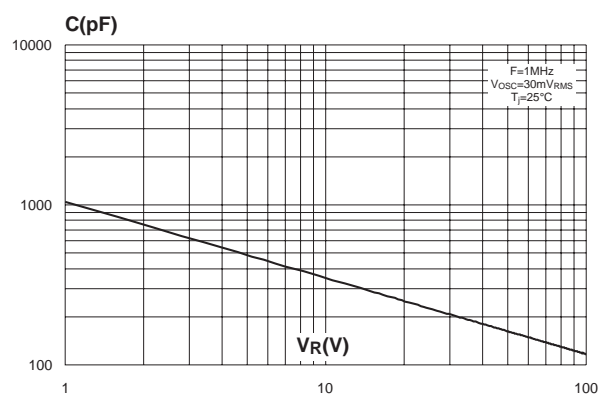
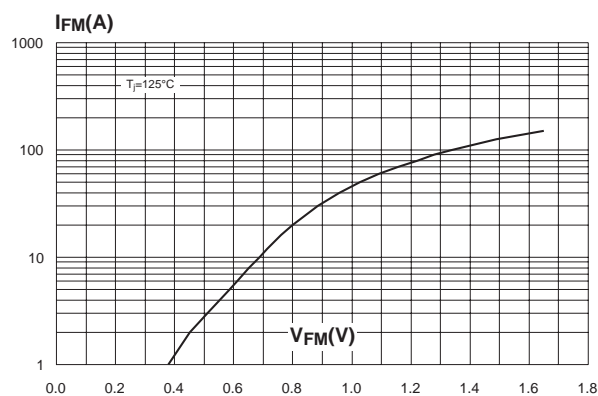


Fig. 7: Forward voltage drop versus forward current (maximum values, per diode).



PACKAGE MECHANICAL DATA

TO-247

REF.	DIMENSIONS					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.85		5.15	0.191		0.203
D	2.20		2.60	0.086		0.102
E	0.40		0.80	0.015		0.031
F	1.00		1.40	0.039		0.055
F1		3.00			0.118	
F2		2.00			0.078	
F3	2.00		2.40	0.078		0.094
F4	3.00		3.40	0.118		0.133
G		10.90			0.429	
H	15.45		15.75	0.608		0.620
L	19.85		20.15	0.781		0.793
L1	3.70		4.30	0.145		0.169
L2		18.50			0.728	
L3	14.20		14.80	0.559		0.582
L4		34.60			1.362	
L5		5.50			0.216	
M	2.00		3.00	0.078		0.118
V		5°			5°	
V2		60°			60°	
Dia.	3.55		3.65	0.139		0.143

- Cooling method : C
- Recommended torque value : 0.8m.N
- Maximum torque value : 1.0m.N

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STPS3060CW	STPS3060CW	TO-247	4.4 g	50	Tube

- Epoxy meets UL94,V0

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